

CooliRIGBT™

Features

- Designed And Qualified for Automotive Applications
- Ultra Fast Switching IGBT: 70-200kHz
- Extremely Low Switching Losses
- Maximum Junction Temperature 175 °C
- Square RBSOA
- Positive $V_{CE(on)}$ Temperature Coefficient

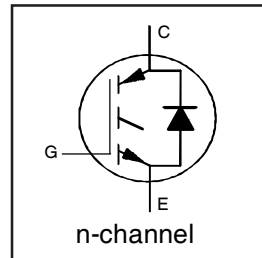
Benefits

- Optimized High Frequency Switching Applications
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation

Applications

- DC-DC Converter
- PFC

ULTRAFAST IGBT WITH ULTRAFAST SOFT RECOVERY DIODE



$$V_{CES} = 600V$$

$$V_{CE(on)} \text{ typ.} = 1.8V$$

$$I_C @ T_C = 100^\circ C = 41A$$

$$T_J \text{ max} = 175^\circ C$$



TO-247AC
AUIRGP65G40D0



TO-247AD
AUIRGF65G40D0

G	C	E
Gate	Collector	Emitter

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGP65G40D0	TO-247AC	Tube	25	AUIRGP65G40D0
AUIRGF65G40D0	TO-247AD	Tube	25	AUIRGF65G40D0

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current ⑥	62	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current ⑥	41	
$I_{NOMINAL}$	Nominal Current @ 200kHz ⑦	20	
I_{CM}	Pulse Collector Current	84	
I_{LM}	Clamped Inductive Load Current ①	112	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	46.1	A
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	30	
I_{FRM}	Maximum Repetitive Forward Current ②	112	
V_{GE}	Gate-to-Emitter Voltage	±20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	625	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	313	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Junction-to-Case-(each IGBT) ④	—	—	0.24	°C/W
$R_{\theta JC}$ (Diode)	Junction-to-Case-(each Diode) ④	—	—	1.78	
$R_{\theta CS}$	Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient (typical socket mount)	—	—	40	
		—	6.0 (0.21)	—	g (oz)

*Qualification standards can be found at <http://www.irf.com/>

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 500\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.18	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$ (25 $^\circ\text{C}$ -175 $^\circ\text{C}$)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.4	—	V	$I_C = 12A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	1.8	2.2		$I_C = 20A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	1.9	—		$I_C = 12A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
		—	2.6	—		$I_C = 20A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
		—	2.2	—		$I_C = 12A, V_{GE} = 15V, T_J = 175^\circ\text{C}$
		—	3.0	—		$I_C = 20A, V_{GE} = 15V, T_J = 175^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-12	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1.0mA$ (25 $^\circ\text{C}$ - 175 $^\circ\text{C}$)
g_{fe}	Forward Transconductance	—	36	—	S	$V_{CE} = 50V, I_C = 20A$
I_{CES}	Collector-to-Emitter Leakage Current	—	3.2	25	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	0.81	—	mA	$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.7	2.45	V	$I_F = 20A$
		—	1.4	—		$I_F = 20A, T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	180	270	nC	$I_C = 20A$
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	28	42		$V_{GE} = 15V$
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	64	96		$V_{CC} = 400V$
E_{on}	Turn-On Switching Loss	—	298	389	μJ	$I_C = 20A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	147	234		$R_G = 4.7\Omega, L = 485\mu H, T_J = 25^\circ\text{C}$
E_{total}	Total Switching Loss	—	445	623		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	35	53	ns	$I_C = 20A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	12	29		$R_G = 4.7\Omega, L = 485\mu H, T_J = 25^\circ\text{C}$
$t_{d(off)}$	Turn-Off delay time	—	142	163		
t_f	Fall time	—	15	32		
E_{on}	Turn-On Switching Loss	—	630	—	μJ	$I_C = 20A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	137	—		$R_G = 4.7\Omega, L = 485\mu H, T_J = 175^\circ\text{C}$
E_{total}	Total Switching Loss	—	767	—		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	33	—	ns	$I_C = 20A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	12	—		$R_G = 4.7\Omega, L = 485\mu H$
$t_{d(off)}$	Turn-Off delay time	—	165	—		$T_J = 175^\circ\text{C}$
t_f	Fall time	—	16	—		
C_{ies}	Input Capacitance	—	4673	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	337	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	58	—		$f = 1.0MHz$
$C_{oes\ eff.}$	Effective Output Capacitance (Time Related) ⑤	—	406	—		$V_{GE} = 0V, V_{CE} = 0V$ to 480V
$C_{oes\ eff. (ER)}$	Effective Output Capacitance (Energy Related) ⑥	—	162	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 80A$ $V_{CC} = 480V, V_p \leq 600V$ $R_G = 4.7\Omega, V_{GE} = +20V$ to 0V
t_{rr}	Diode Reverse Recovery Time	—	41	—	ns	$T_J = 25^\circ\text{C} \quad I_F = 20A, V_R = 200V,$
		—	70	—		$T_J = 125^\circ\text{C} \quad di/dt = 200A/\mu s$
Q_{rr}	Diode Reverse Recovery Charge	—	116	—	nC	$T_J = 25^\circ\text{C} \quad I_F = 20A, V_R = 200V,$
		—	580	—		$T_J = 125^\circ\text{C} \quad di/dt = 200A/\mu s$
I_{rr}	Peak Reverse Recovery Current	—	4.8	—	A	$T_J = 25^\circ\text{C} \quad I_F = 20A, V_R = 200V,$
		—	7.2	—		$T_J = 125^\circ\text{C} \quad di/dt = 200A/\mu s$

Notes ① through ⑦ are on page 13

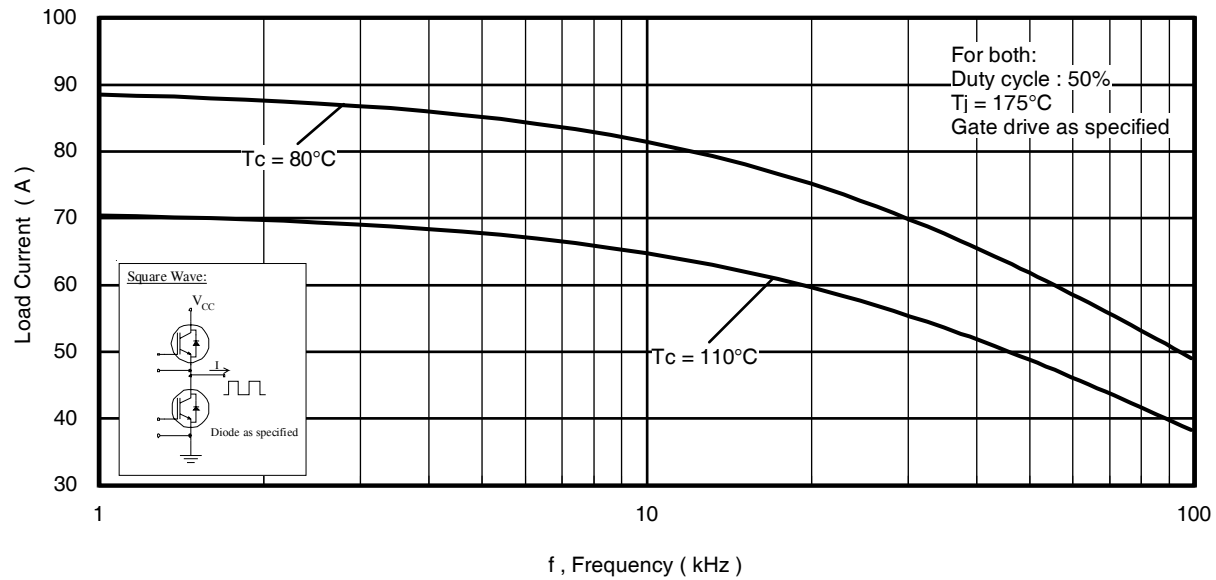


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = IRMS of fundamental)

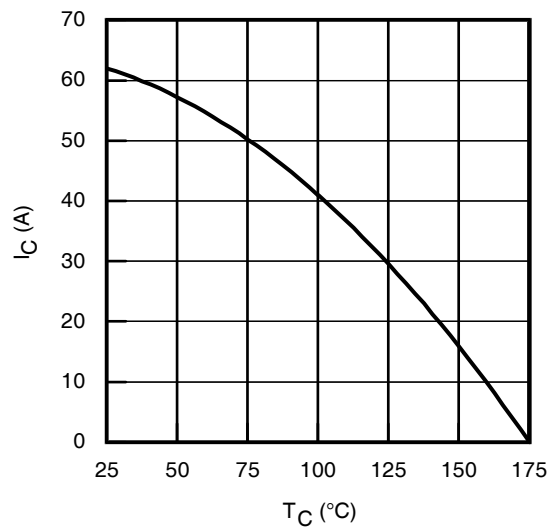


Fig. 2 - Maximum DC Collector Current vs. Case Temperature

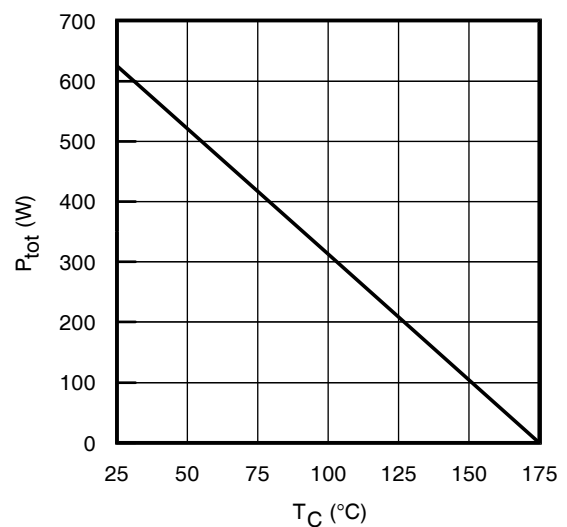


Fig. 3 - Power Dissipation vs. Case Temperature

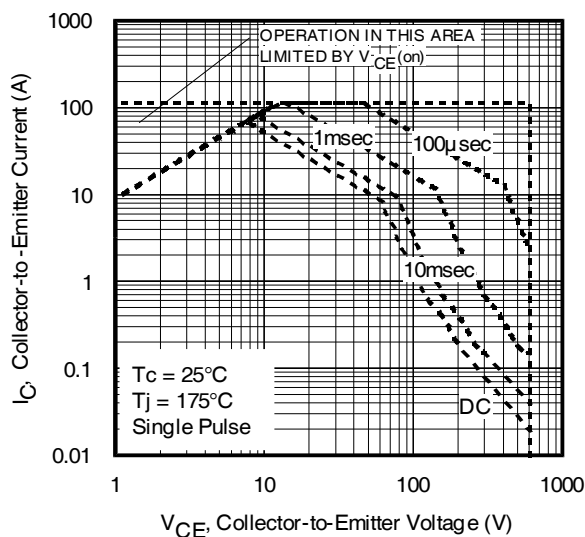


Fig. 4 - Forward SOA
 $T_C = 25^\circ\text{C}$; $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

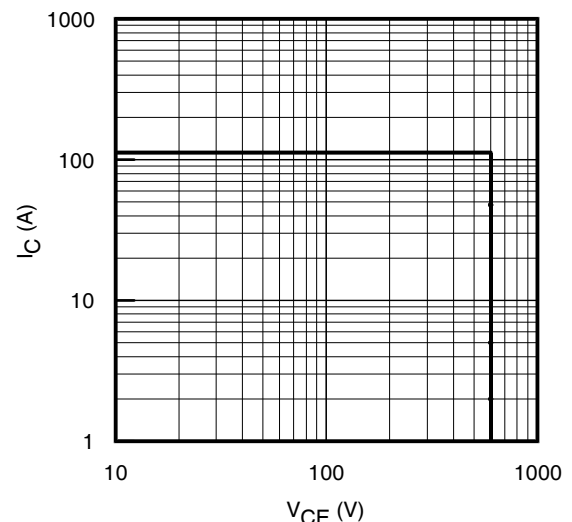


Fig. 5 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 20\text{V}$

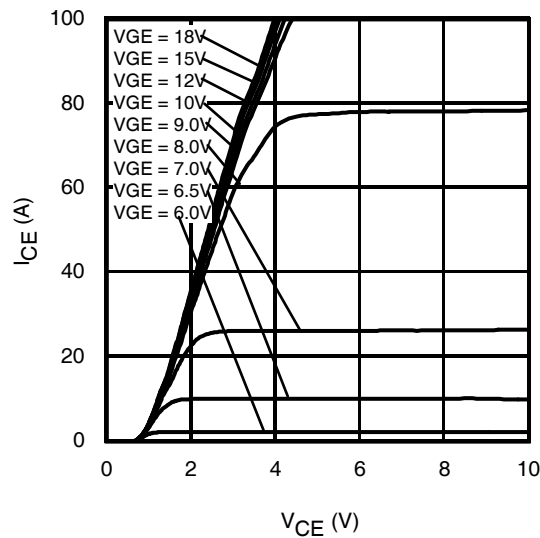


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = -40^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

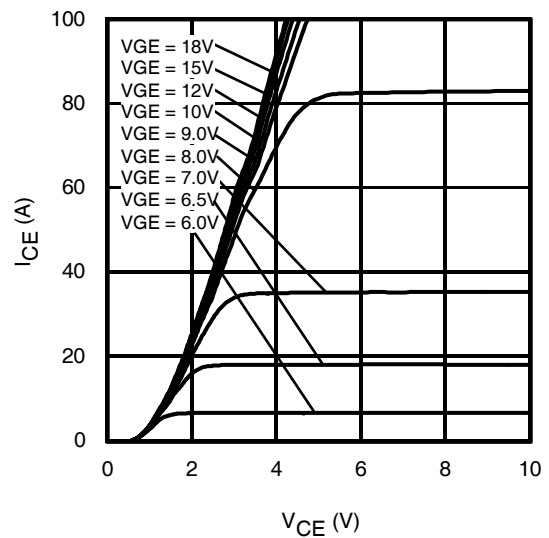


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

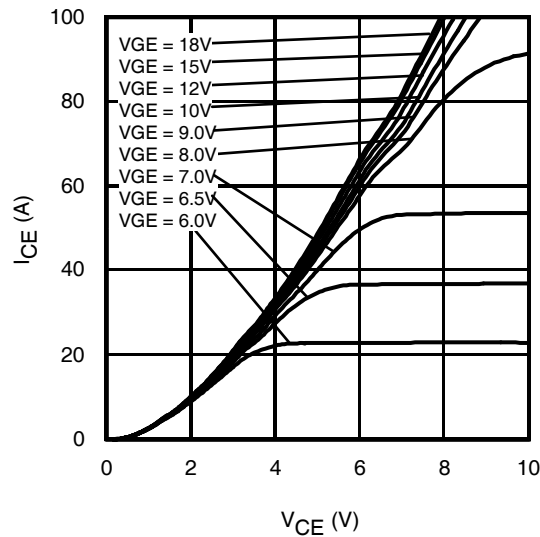


Fig. 8 - Typ. IGBT Output Characteristics
 $T_J = 175^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

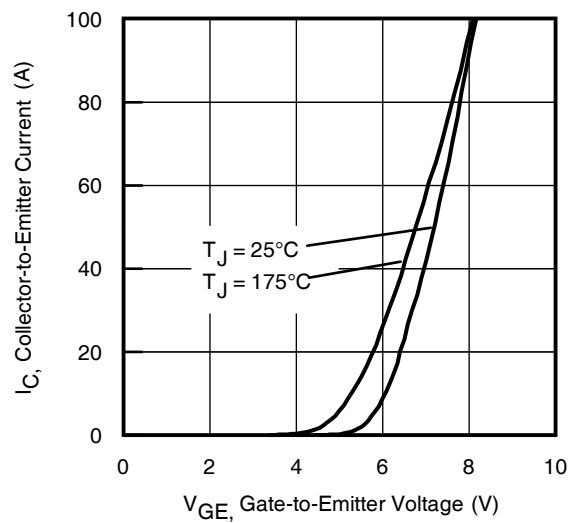


Fig. 9 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 30\mu\text{s}$

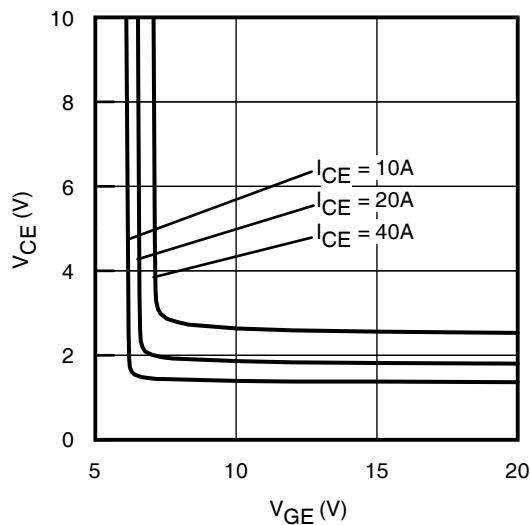


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^{\circ}\text{C}$

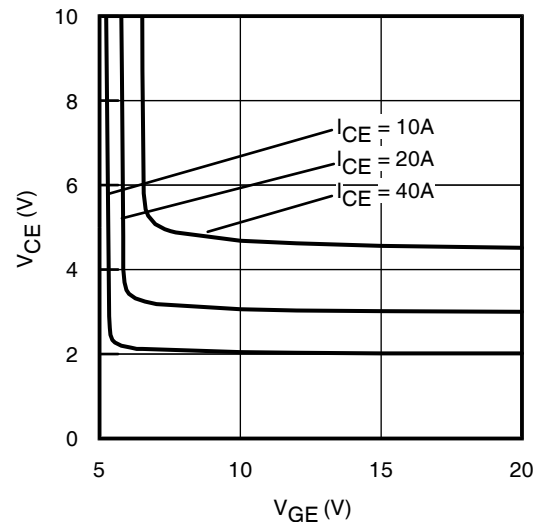


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^{\circ}\text{C}$

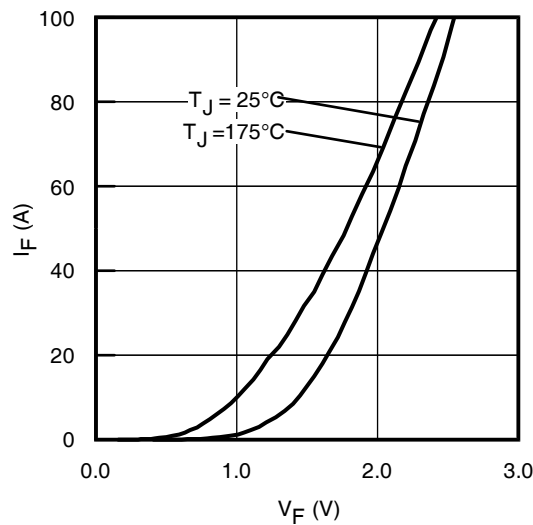


Fig. 12 - Typ. Diode Forward Characteristics
 $t_p = 30\mu s$

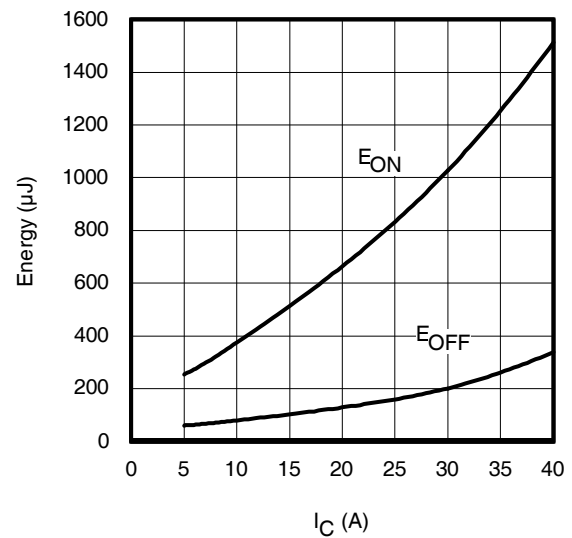


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ C$; $L = 0.49mH$; $V_{CE} = 400V$; $R_G = 4.7\Omega$; $V_{GE} = 15V$

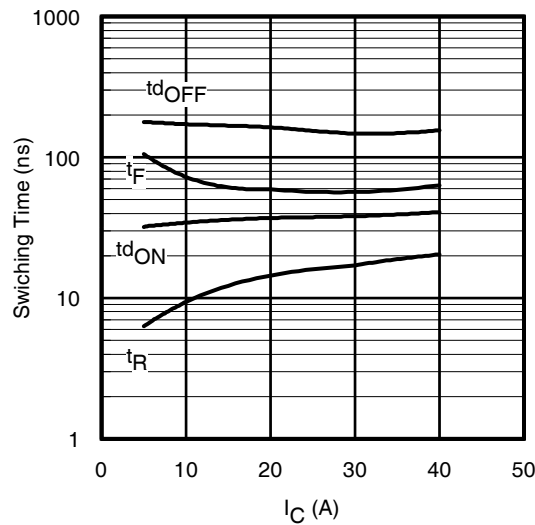


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ C$; $L = 0.49mH$; $V_{CE} = 400V$; $R_G = 4.7\Omega$; $V_{GE} = 15V$

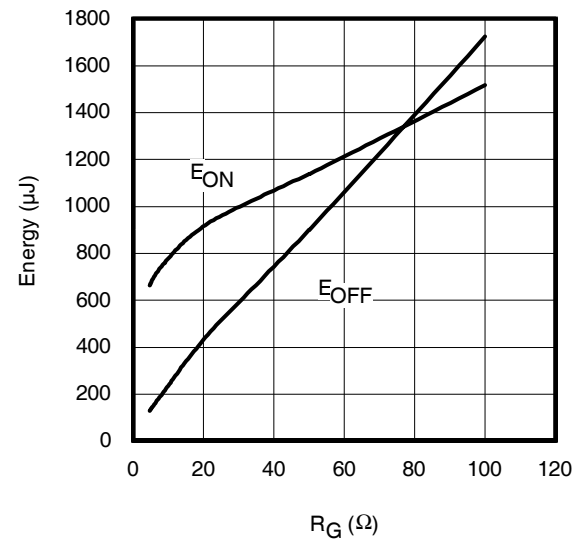


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ C$; $L = 0.49mH$; $V_{CE} = 400V$; $I_{CE} = 20A$; $V_{GE} = 15V$

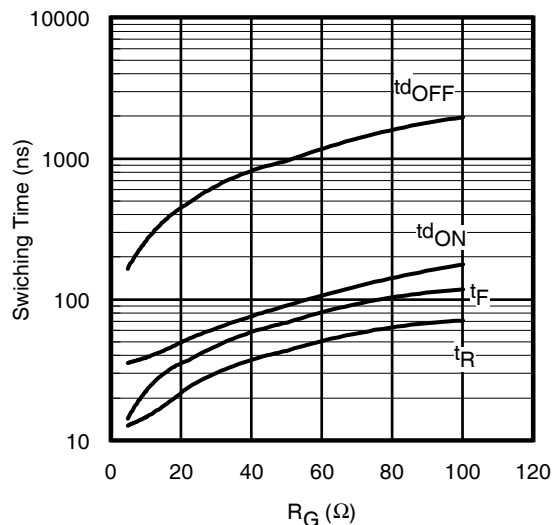


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ C$; $L = 0.49mH$; $V_{CE} = 400V$; $I_{CE} = 20A$; $V_{GE} = 15V$

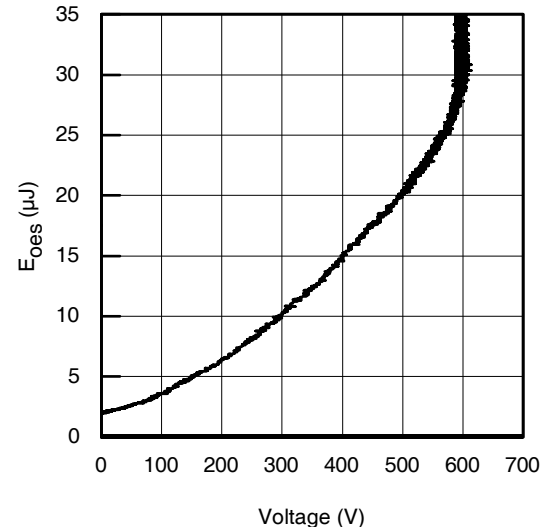


Fig. 17 - Typ. Output Capacitance
Stored Energy vs. V_{CE}

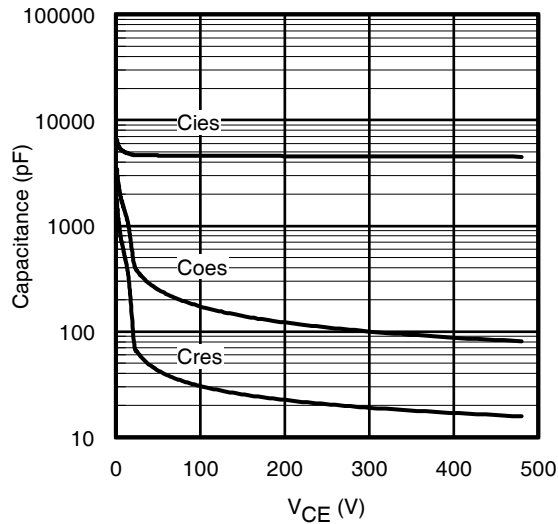


Fig. 18 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

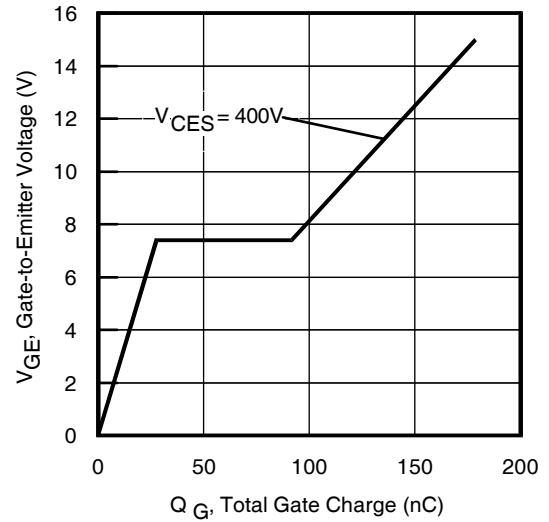


Fig. 19 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 20A$; $L = 200\mu H$

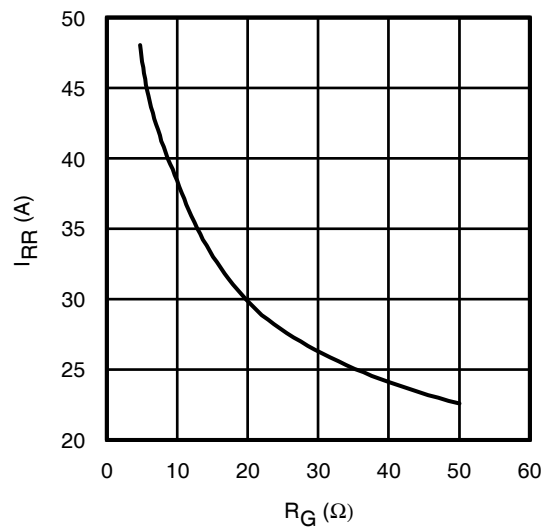
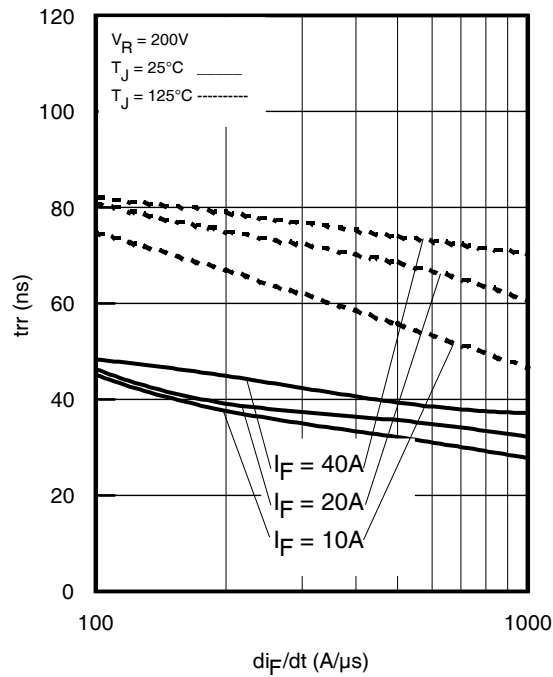
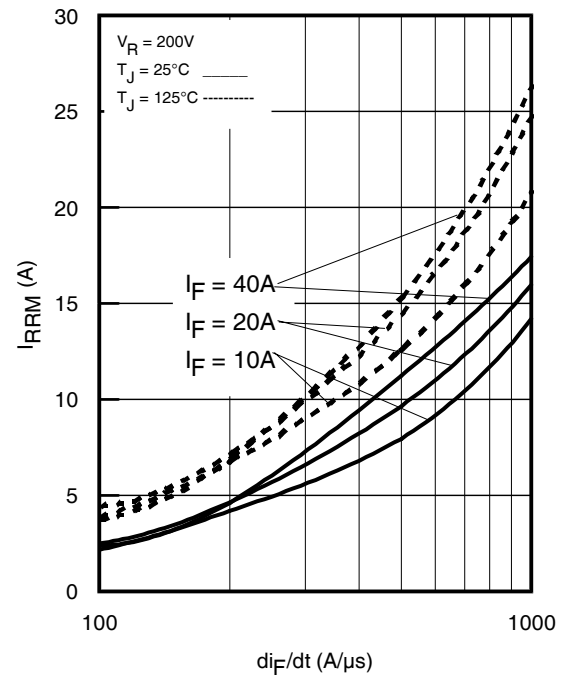
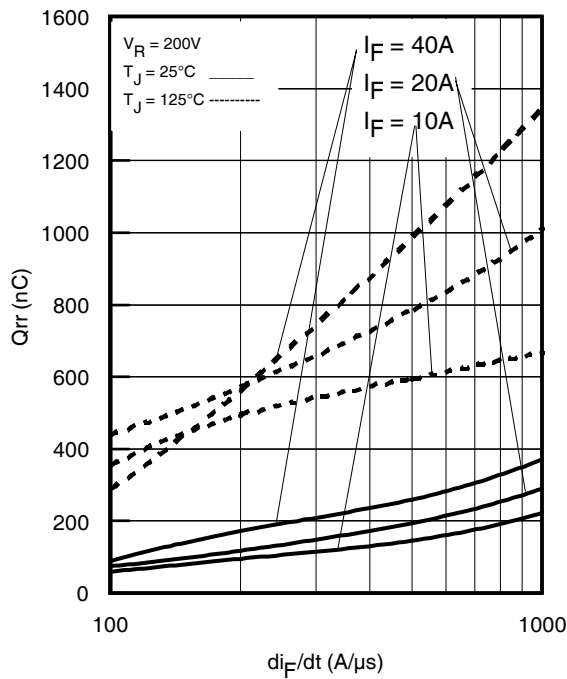
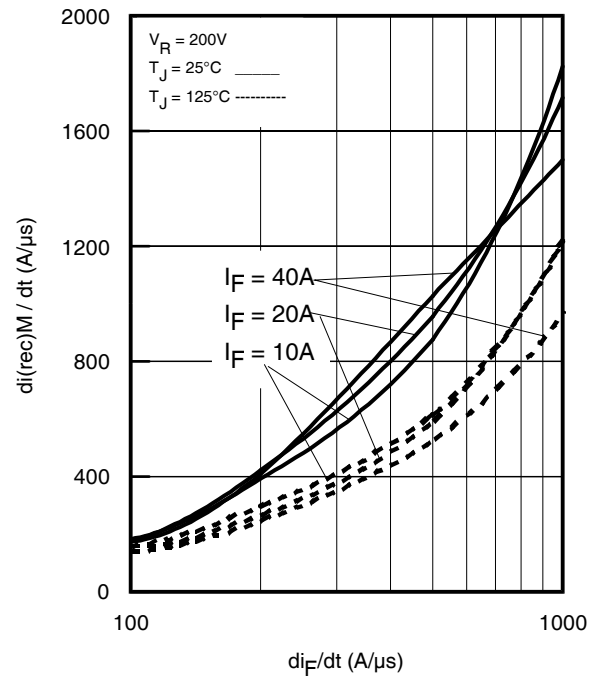


Fig. 20 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ C$


Fig. 21 - Typical Reverse Recovery vs. di_F/dt

Fig. 22 - Typical Recovery Current vs. di_F/dt

Fig. 23 - Typical Stored Charge vs. di_F/dt

Fig. 24 - Typical $di_{(rec)M}/dt$ vs. di_F/dt ,

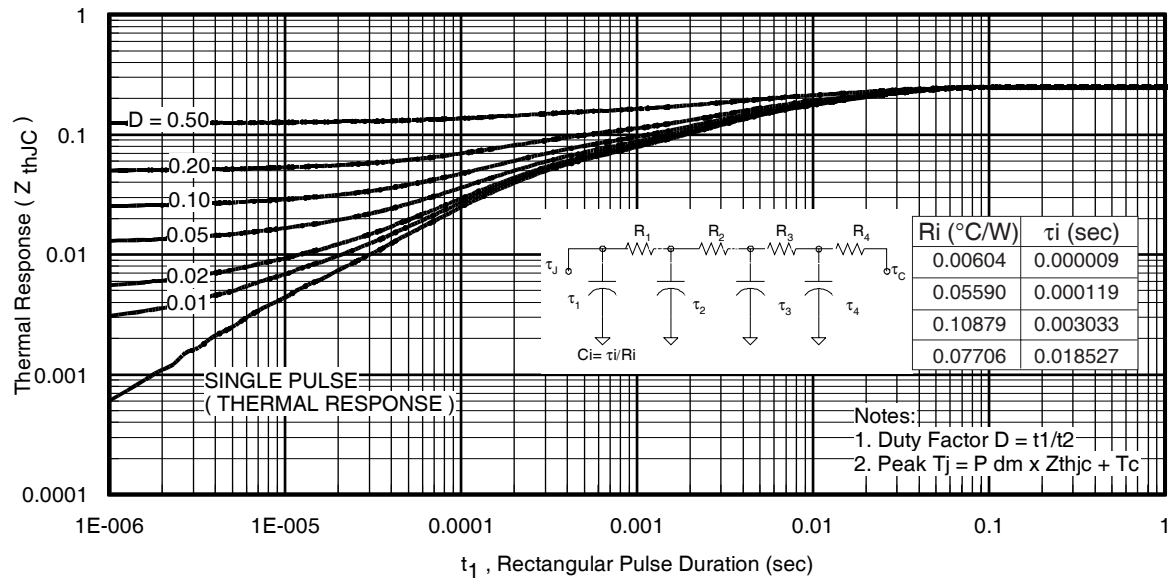


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

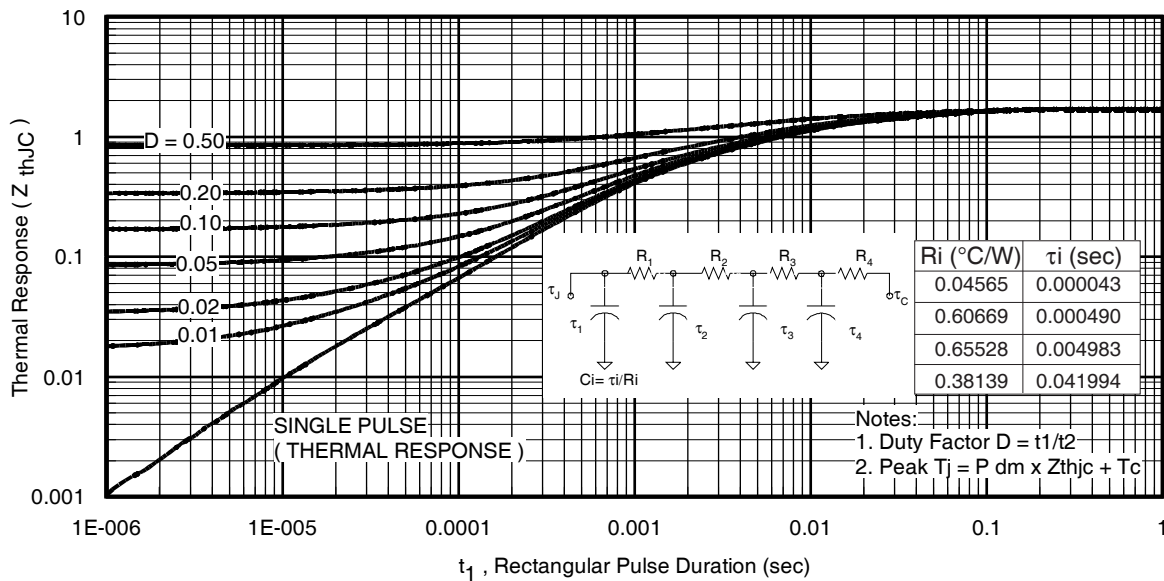
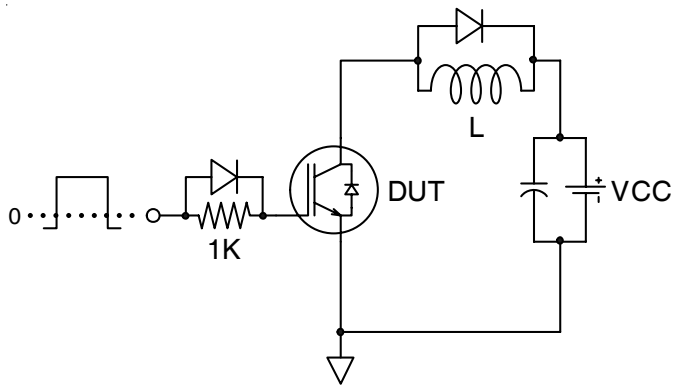
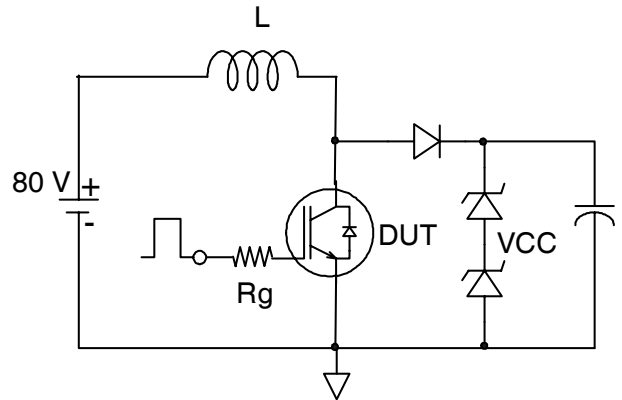
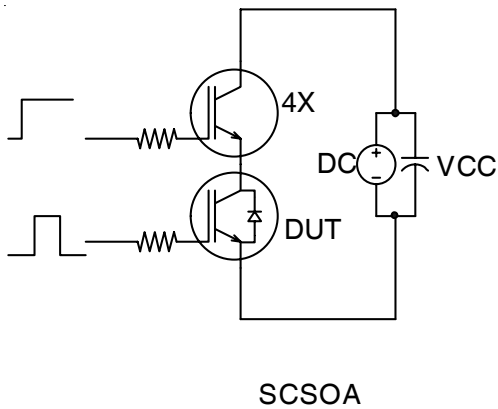
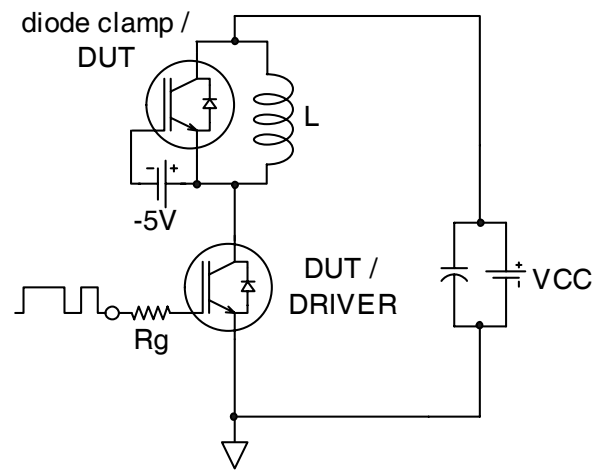
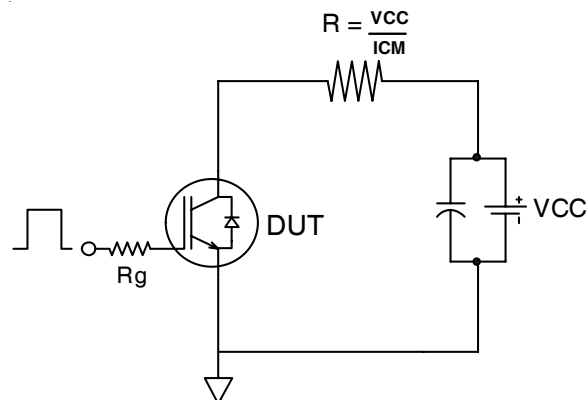


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit

Fig.C.T.5 - Resistive Load Circuit

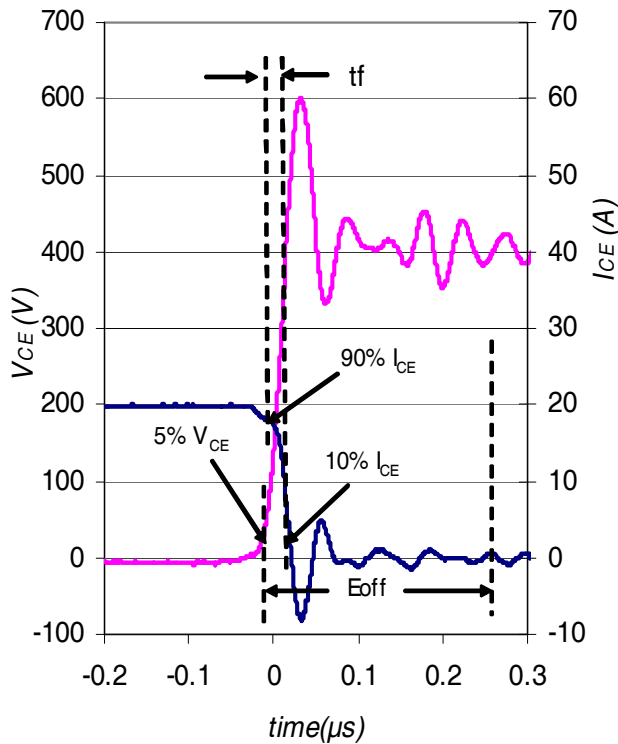


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

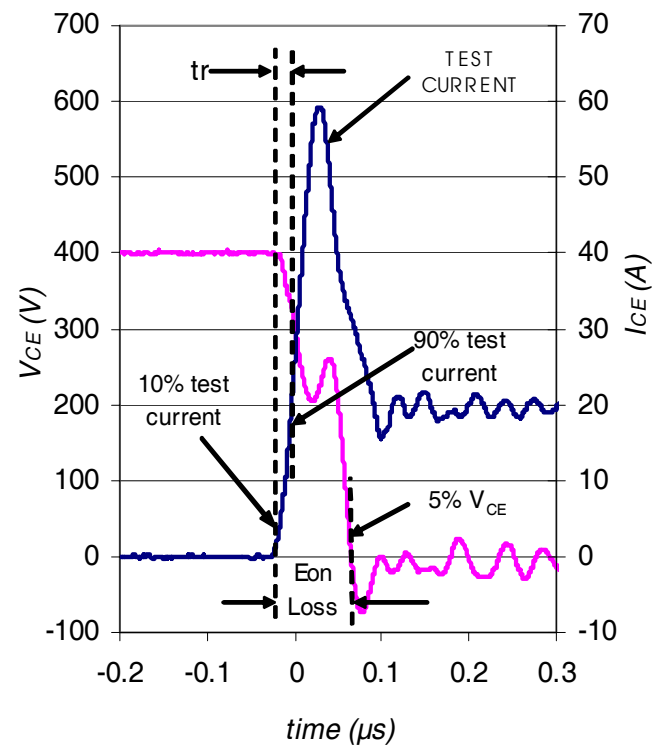


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

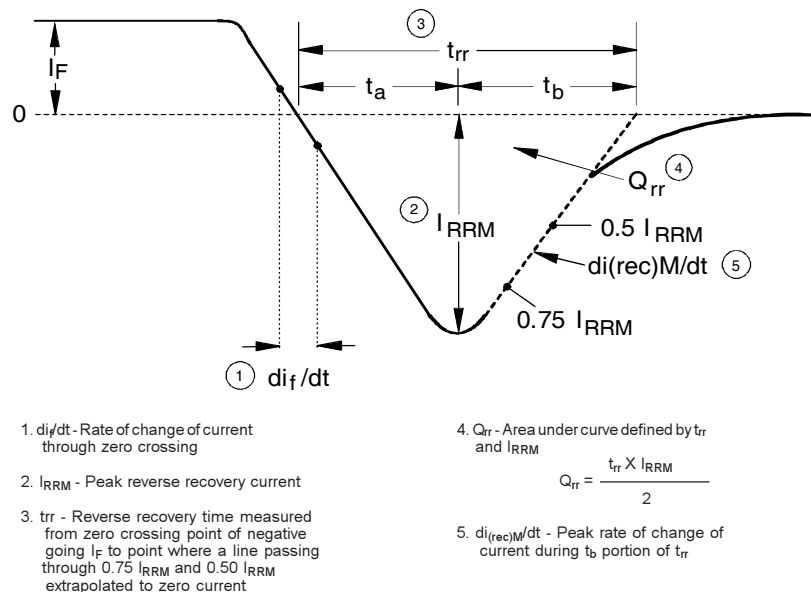
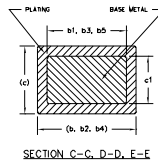
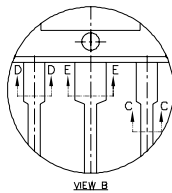
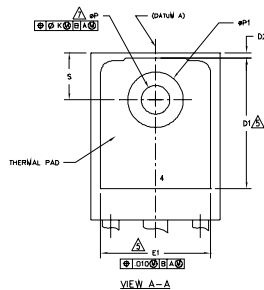
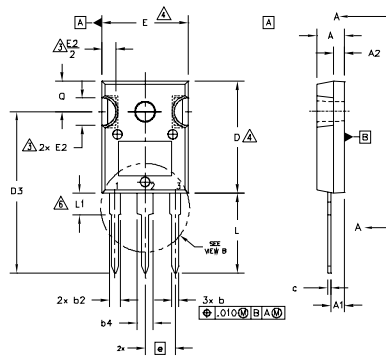


Fig. WF3 - Reverse Recovery Waveform and Definitions

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTE
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
D3	1.122	1.161	28.50	29.50	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

PART NUMBERS AFFECTED:

AUIRG4PH50S
AUIRG4066D1/E
AUIRG4063D/E
AUIRG50B60PD1/E
AUIRG4062D1/E
AUIRG65A20D0
AUIRG65G20D0
AUIRG/F66524D0
AUIRG/F76524D0
AUIRG/F66548D0
AUIRG/F76548D0

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

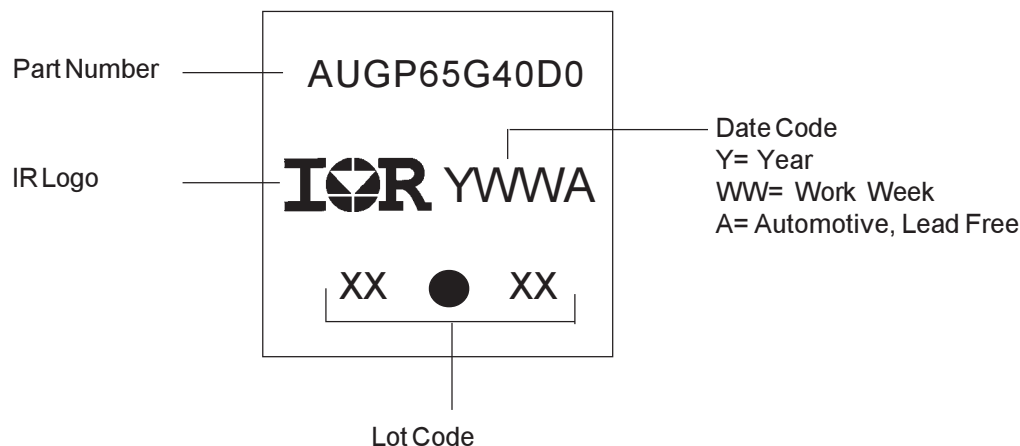
DIODES

- | | |
|---------------|----------------|
| 1.- GATE | 1.- ANODE/OPEN |
| 2.- COLLECTOR | 2.- CATHODE |
| 3.- EMITTER | 3.- ANODE |
| 4.- COLLECTOR | |

SPECIAL NOTE:

- a) ADDED D3 FOR SPECIAL REQUIREMENT

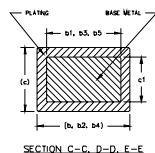
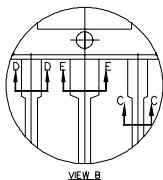
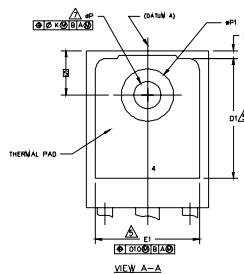
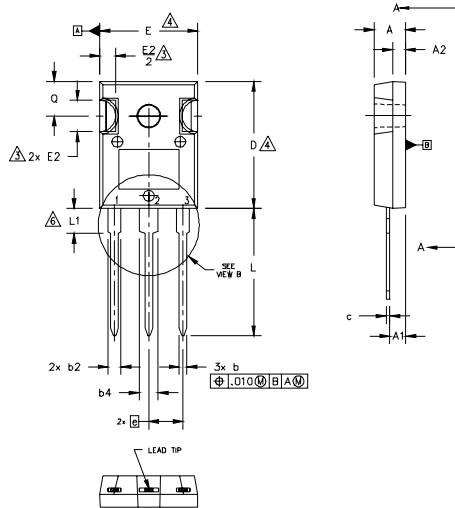
TO-247AC Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.— GATE
- 2.— DRAIN
- 3.— SOURCE
- 4.— DRAIN

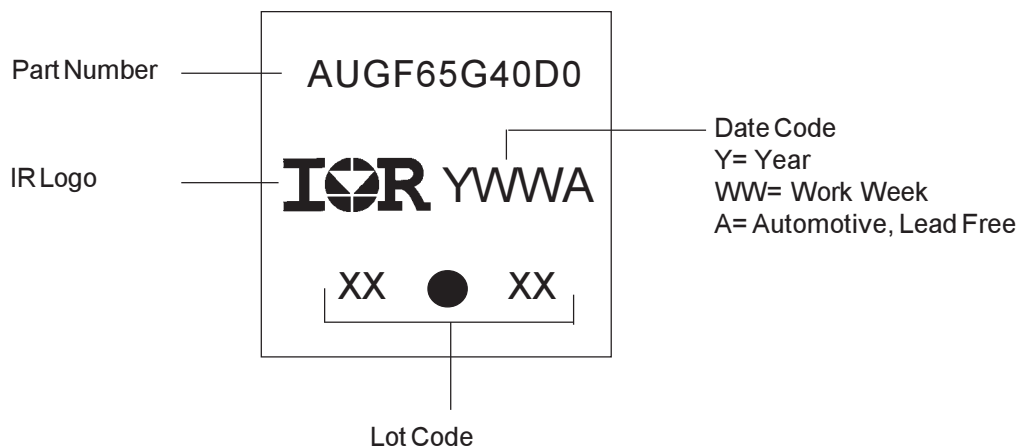
IGBTs, CoPACK

- 1.— GATE
- 2.— COLLECTOR
- 3.— EMITTER
- 4.— COLLECTOR

DIODES

- 1.— ANODE/OPEN
- 2.— CATHODE
- 3.— ANODE

TO-247AD Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-247AC	N/A
		TO-247AD	N/A
ESD	Machine Model	Class M4 (+/- 400V) ^{††} AEC-Q101-002	
	Human Body Model	Class H3B (+/- 8000V) ^{††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1000V) ^{††} AEC-Q101-005	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com>

^{††} Highest passing voltage.

Notes:

- ① $V_{CC} = 80\% (V_{CES})$, $V_{GE} = 20V$, $L = 485\mu H$, $R_G = 4.7\Omega$, tested in production $I_{LM} \leq 400A$.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ R_{θ} is measured at T_J of approximately $90^{\circ}C$.
- ⑤ C_{oes} eff. is a fixed capacitance that gives the same charging time as C_{oes} while V_{CE} is rising from 0 to 80% V_{CES} . C_{oes} eff.(ER) is a fixed capacitance that stores the same energy as C_{oes} while V_{CE} is rising from 0 to 80% V_{CES} .
- ⑥ Calculated continuous current based on maximum allowable junction temperature.
- ⑦ Nominal current limit is suggested for 400V, 200kHz operation. Actual current rating varies with application and is subjected to T_J and SOA limits.

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For technical support, please contact IR's Technical Assistance Center
<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

101 N. Sepulveda Blvd., El Segundo, California 90245
 Tel: (310) 252-7105

Revision History

Date	Comments
9/8/2015	Removed "short circuit rating on page 1 & 2.